

X-Parameters: The Power to Create a Paradigm Shift in Nonlinear Design?

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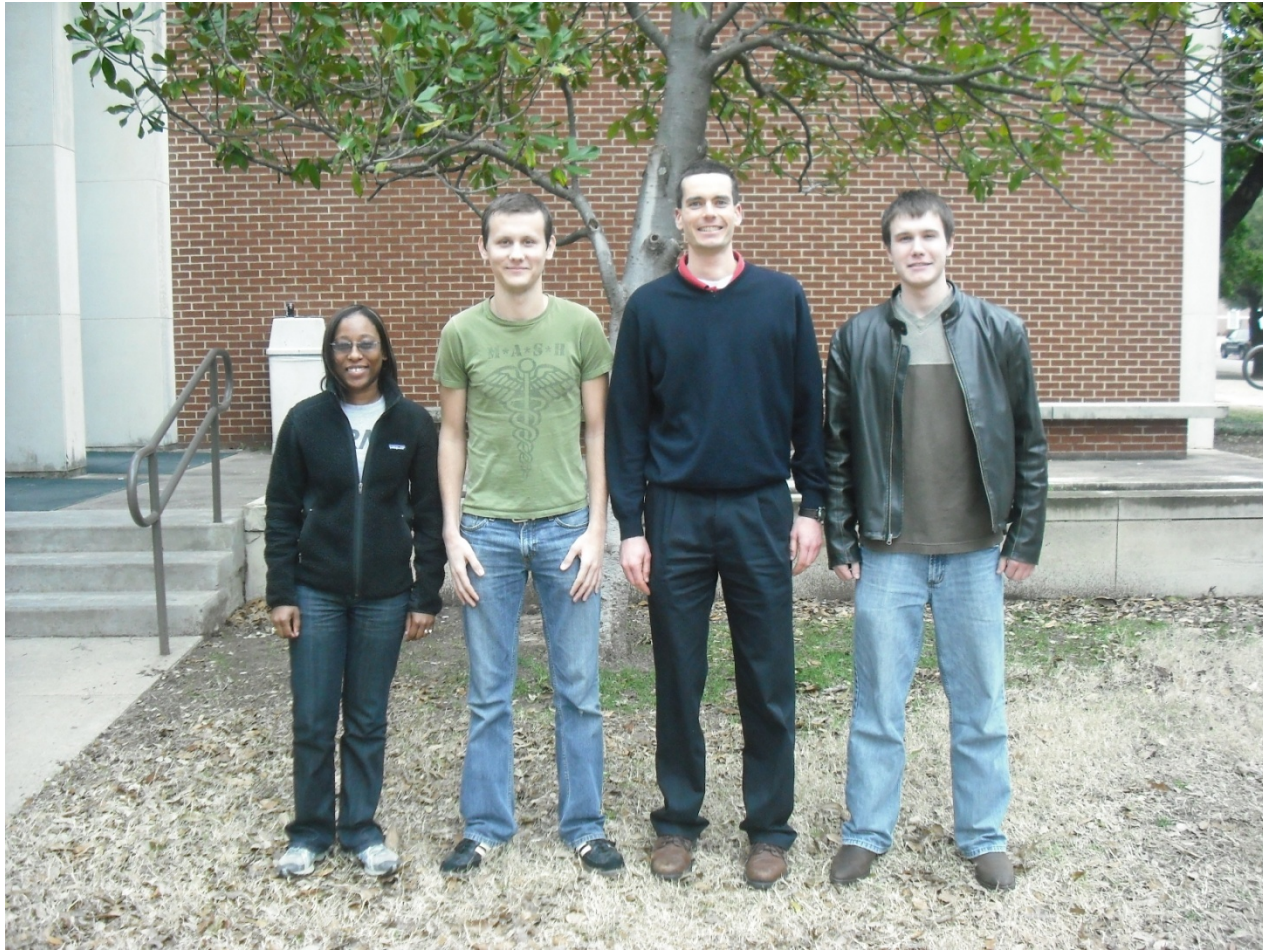
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- X-Parameters is a registered trademark of Agilent Technologies.

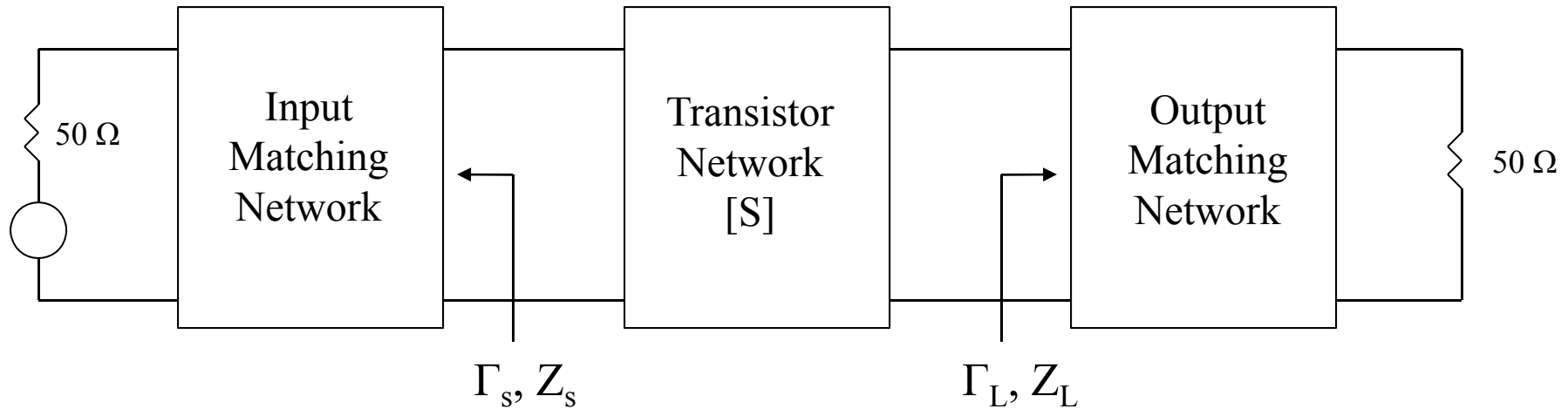
WMCS Active Circuit Research Group



Agenda

- The Microwave Amplifier Design Problem
- Linear Network Parameters
- X-Parameters for Nonlinear Devices
- Research Goals
- Conclusions

The Microwave Amplifier Design Problem*



- Small-signal design is based solely on the S-parameters of the transistor network.
- Γ_s (or Z_s) and Γ_L, Z_L are chosen for design criteria including gain, efficiency, linearity, stability, and noise figure.

*G. Gonzalez, *Microwave Transistor Amplifiers: Analysis and Design*, Second Edition, Prentice-Hall, 1997.

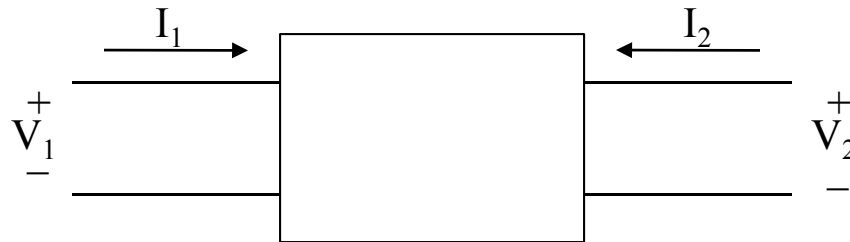
Small-Signal vs. Large-Signal

- Small-Signal
 - We “bias” the device and then superimpose a very small ($\rightarrow 0$) AC waveform.
 - Designs can be based on S-parameters of the active device.
- Large-Signal
 - The AC signal on top of the DC bias cannot be considered of negligible amplitude.
 - Nonlinear models or measurements must be used to design.

Small-Signal Design

- Can be accomplished using linear network parameters.
- The measurement is all you need!
- Can calculate gain, noise figure, and stability as a function of
 - Device S-parameters
 - Source and load terminating impedances

Small-Signal Z-Parameters



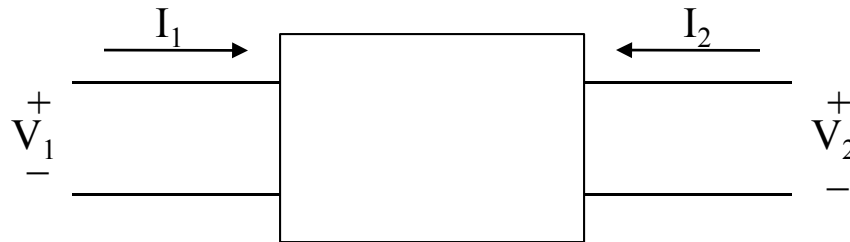
$$V_1 = Z_{11}I_1 + Z_{12}I_2$$

$$V_2 = Z_{21}I_1 + Z_{22}I_2$$

$$Z_{11} = \left. \frac{V_1}{I_1} \right|_{I_2=0} \quad Z_{21} = \left. \frac{V_2}{I_1} \right|_{I_2=0} \quad Z_{12} = \left. \frac{V_1}{I_2} \right|_{I_1=0} \quad Z_{22} = \left. \frac{V_2}{I_2} \right|_{I_1=0}$$

- Open-circuit appropriate port.
- Apply current.
- Measure voltage.

Small-Signal Y-Parameters



$$I_1 = Y_{11}V_1 + Y_{12}V_2$$

$$I_2 = Y_{21}V_1 + Y_{22}V_2$$

$$Y_{11} = \left. \frac{I_1}{V_1} \right|_{V_2=0}$$

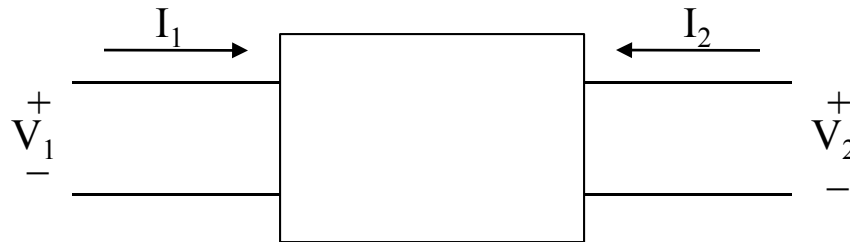
$$Y_{21} = \left. \frac{I_2}{V_1} \right|_{V_2=0}$$

$$Y_{12} = \left. \frac{I_1}{V_2} \right|_{V_1=0}$$

$$Y_{22} = \left. \frac{I_2}{V_2} \right|_{V_1=0}$$

- Short-circuit appropriate port.
- Apply voltage.
- Measure current.

Small-Signal Y-Parameters



$$I_1 = Y_{11}V_1 + Y_{12}V_2$$

$$I_2 = Y_{21}V_1 + Y_{22}V_2$$

$$Y_{11} = \left. \frac{I_1}{V_1} \right|_{V_2=0}$$

$$Y_{21} = \left. \frac{I_2}{V_1} \right|_{V_2=0}$$

$$Y_{12} = \left. \frac{I_1}{V_2} \right|_{V_1=0}$$

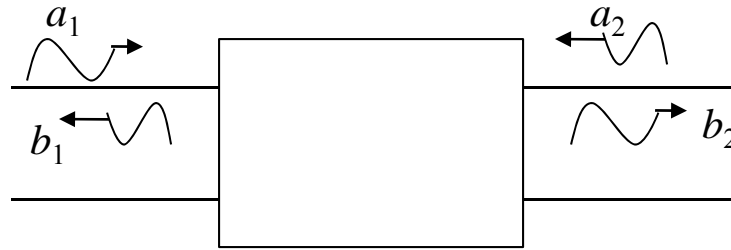
$$Y_{22} = \left. \frac{I_2}{V_2} \right|_{V_1=0}$$

- Short-circuit appropriate port.
- Apply voltage.
- Measure current.

Small-Signal S-Parameters

- Traveling voltage waves are easier to measure at microwave frequencies than total voltage and current.
- Divide V_1 into two components:
 - a_1 = voltage wave entering the network
 - b_1 = voltage wave leaving the network
- Divide V_2 into two components:
 - a_2 = voltage wave entering the network
 - b_2 = voltage wave leaving the network

Small-Signal S-Parameters



$$b_1 = S_{11}a_1 + S_{12}a_2$$

$$b_2 = S_{21}a_1 + S_{22}a_2$$

$$S_{11} = \left. \frac{b_1}{a_1} \right|_{a_2=0}$$

$$S_{21} = \left. \frac{b_2}{a_1} \right|_{a_2=0}$$

$$S_{12} = \left. \frac{b_1}{a_2} \right|_{a_1=0}$$

$$S_{22} = \left. \frac{b_2}{a_2} \right|_{a_1=0}$$

- Make sure no reflections occur from appropriate port (terminate it in Z_0).
- Apply incident wave to the other port.
- Measure wave leaving appropriate port.

Small-Signal S-Parameters

- Can be easily measured with a vector network analyzer (VNA):



- Can be calculated from Y or Z parameters (and vice versa).

Small-Signal Amplifier Design

Gain Equations

- Based only on S-parameters and source/load terminating impedances:

$$G_p = \frac{1}{1 - \Gamma_{IN}} |S_{21}|^2 \frac{1 - |\Gamma_L|^2}{|1 - S_{22}\Gamma_L|^2}$$

where

$$\Gamma_{IN} = S_{11} + \frac{S_{12} S_{21} \Gamma_L}{1 - S_{22} \Gamma_L}$$

Small-Signal Amplifier Optimum Load and Source Impedances

- Can be calculated directly from S-parameters:

$$\Gamma_{Ms} = \frac{B_1 \pm \sqrt{B_1^2 - 4|C_1|^2}}{2C_1} \quad \Gamma_{ML} = \frac{B_2 \pm \sqrt{B_2^2 - 4|C_2|^2}}{2C_2}$$

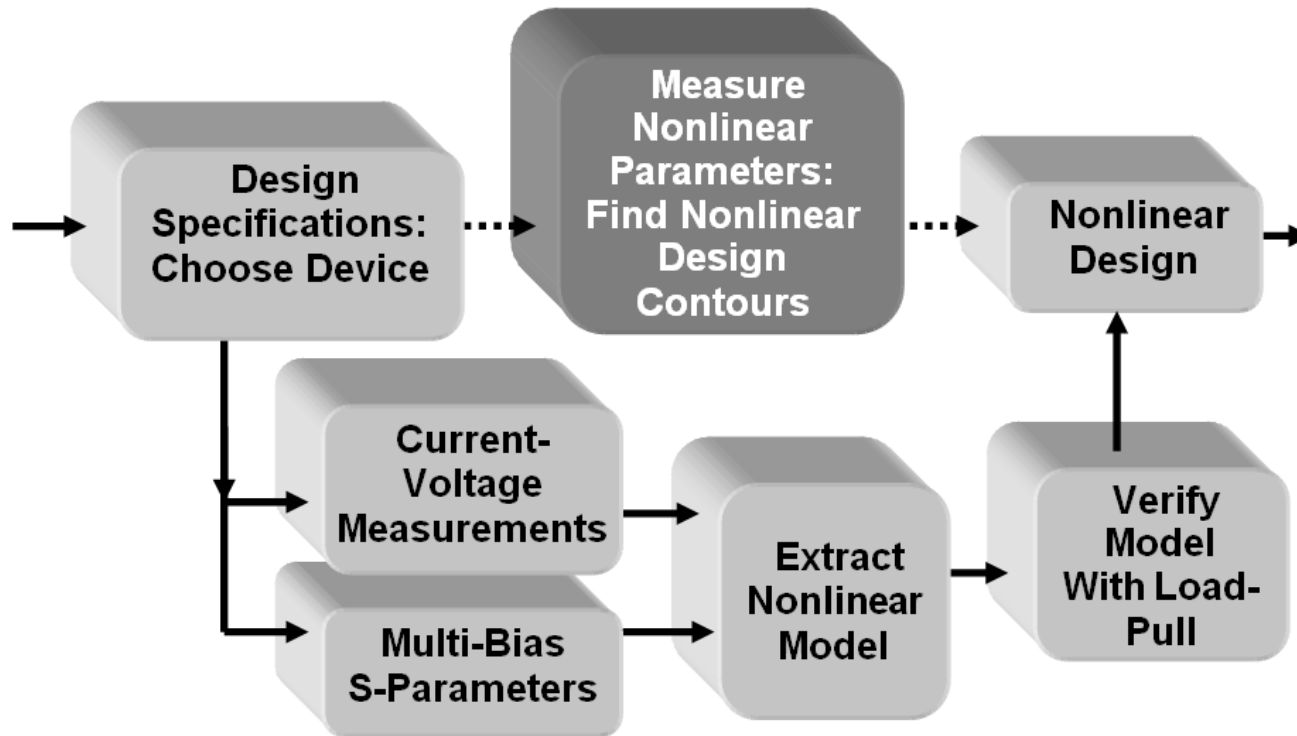
(B_1 , B_2 , C_1 , C_2 are functions of [S].)

- Contours of equal gain (less than maximum), noise, and stability circles can be plotted on the complex Γ_L and/or Γ_s planes (Smith Charts)

Large-Signal Amplifier Design

- Without nonlinear network parameters, requires bench-top load pull or an accurate nonlinear transistor model.
- Nonlinear transistor model extraction requires
 - Current-voltage measurement(s)
 - S-Parameters at multiple transistor bias points.
 - A skilled engineer to do the extraction (20 to 50 parameters!)
 - Load-pull measurements for validation
- Is there a method analogous to the small-signal S-parameters using X-parameters that can predict large-signal gain?
- TOI? ACPR?, etc.

Revolutionizing the Nonlinear Design Cycle: Nonlinear Network Parameters

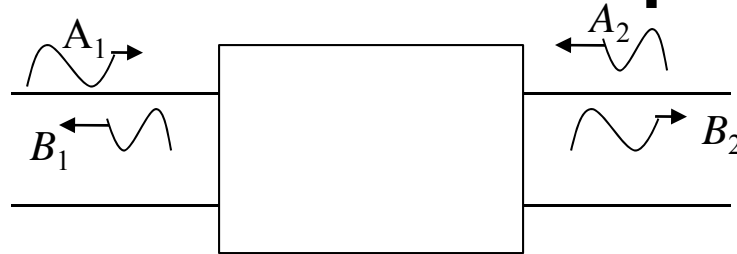


Agilent X-Parameters*

- Allow network characterization in a method similar to small-signal.
- Measurements required:
 - Signal Magnitude (Input and Output)
 - Signal Phase (Input and Output)
- Calibrations required:
 - Magnitude at fundamental and all harmonics
 - Phase at fundamental (can skip harmonics?)

*X-parameters is a registered trademark of Agilent Technologies.

X-Parameter Equation*



$$B_{ef} = X_{ef}^{(F)}(|A_{11}|)P^f + \sum_{g,h} X_{ef,gh}^{(S)}(|A_{11}|)P^{f-h}a_{gh} + \sum_{g,h} X_{ef,gh}^{(T)}(|A_{11}|)P^{f+h}a_{gh}^*$$

Each X parameter is a function of $|A_{11}|$.

$P = e^{j\angle A_{11}}$ provides phase correction for harmonic conversion.

$X^{(S)}$
 ef, gh

Arrival Port

Arrival Harmonic

Departure Port

Departure Harmonic

*D. Root, "A New Paradigm for Measurement, Modeling, and Simulation of Nonlinear Microwave and RF Components," Presentation at Berkeley Wireless Research Center, April 2009.

X-Parameter Equation

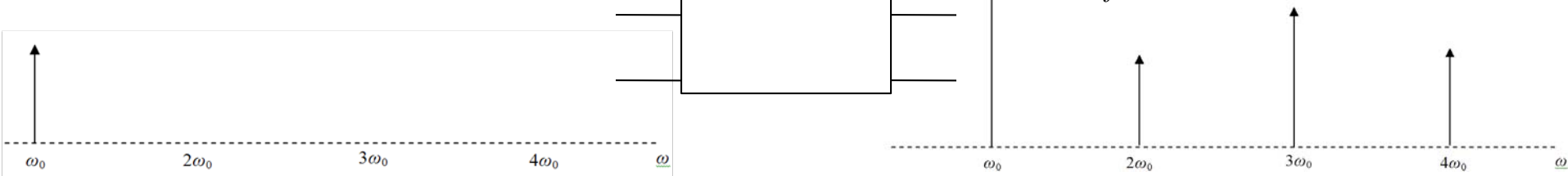
$$B_{ef} = X_{ef}^{(F)}(|A_{11}|)P^f + \sum_{g,h} X_{ef,gh}^{(S)}(|A_{11}|)P^{f-h}a_{gh} + \sum_{g,h} X_{ef,gh}^{(T)}(|A_{11}|)P^{f+h}a_{gh}^*$$

- First Term: Output at port e and harmonic f due to large-signal input at port 1 and fundamental.
- Second and Third Terms: Output at port e and harmonic f due to small-signal perturbations perturbations at all ports and harmonics.

Measuring 2-Port X-Parameters

$$X_{ef}^{(F)}$$

$$B_{ef} = \underbrace{X_{ef}^{(F)}(|A_{11}|)P^f}_{A_{11}} + \sum_{g,h} X_{ef,gh}^{(S)}(|A_{11}|)P^{f-h}a_{gh} + \sum_{g,h} X_{ef,gh}^{(T)}(|A_{11}|)P^{f+h}a_{gh}^*$$



- Negative-frequency side of Fourier spectrum is identical.
- a_{gh}, a_{gh}^* (small signals) set to zero.
- Measure magnitude and phase of output harmonics at ports 1 and 2 .

$$X_{ef}^{(F)}(|A_{11}|) = \frac{B_{ef}}{P^f}$$

Measuring 2-Port X-Parameters

$$B_{ef} = X_{ef}^{(F)} (|A_{11}|) P^f + \sum_{g,h} X_{ef,gh}^{(S)} (|A_{11}|) P^{f-h} a_{gh} + \sum_{g,h} X_{ef,gh}^{(T)} (|A_{11}|) P^{f+h} a_{gh}^*$$

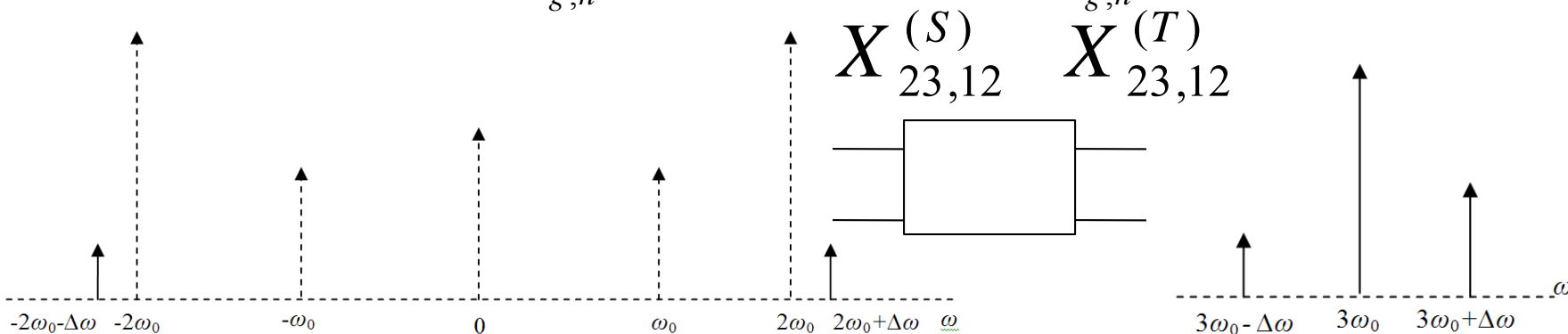


Figure 4. Frequency Content of the Input Cosine Signal $a_{12} + a_{12}^*$

Figure 2. Frequency Content of the Output Component B_{23}

$$a_{gh} + a_{gh}^* = 2 \operatorname{Re}(a_{gh})$$

- A cosine input has positive and negative frequency content.
- Mixing is caused by the nonlinearities, causing two sums to arise at each frequency; one from the negative frequency and one from the positive frequency.

Measuring 2-Port X-Parameters

$$B_{ef} = X_{ef}^{(F)} (|A_{11}|) P^f + \sum_{g,h} X_{ef,gh}^{(S)} (|A_{11}|) P^{f-h} a_{gh} + \sum_{g,h} X_{ef,gh}^{(T)} (|A_{11}|) P^{f+h} a_{gh}^*$$

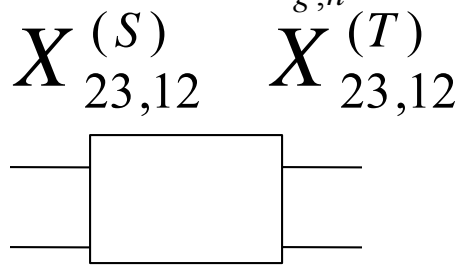
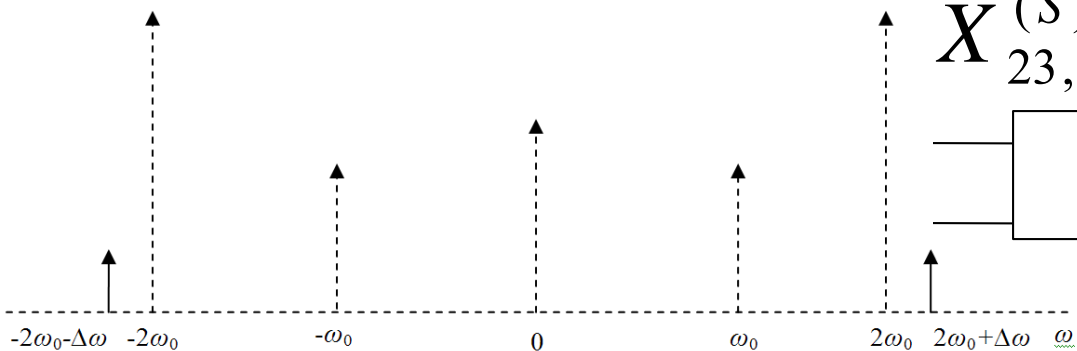


Figure 4. Frequency Content of the Input Cosine Signal $a_{12} + a_{12}^*$

Figure 2. Frequency Content of the Output Component B_{23}

$$a_{gh} + a_{gh}^* = 2 \operatorname{Re}(a_{gh})$$

- In this case, conversion by addition to $3\omega_0$ from $2\omega_0$ can be accomplished by adding ω_0 and from $-2\omega_0$ by adding $5\omega_0$.
- The P exponential is the number of harmonics added to perform each conversion.
- Terms from a_{gh} is above the destination frequency and the term from a_{gh}^* is slightly below the destination frequency.

Measuring 2-Port X-Parameters

$$X_{23,12}^{(S)} \quad X_{23,12}^{(T)}$$

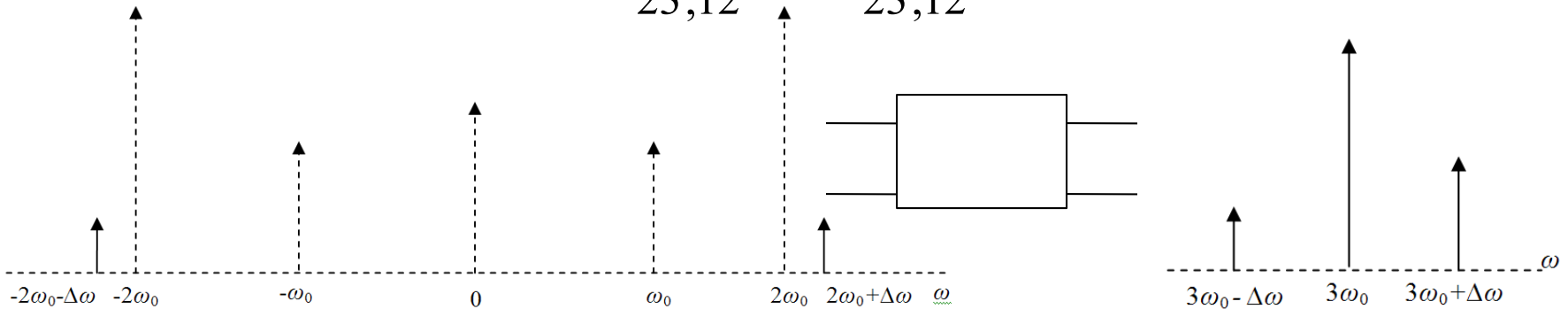


Figure 4. Frequency Content of the Input Cosine Signal $a_{12} + a_{12}^*$

Figure 2. Frequency Content of the Output Component B_{23}

High Term, Cosine Measurement:
$$X_{ef,gh}^{(S)} = \frac{|B_{ef}(\text{cosine}, \text{high})| e^{j\theta}}{P^{f-h} a_{gh}}$$

Low Term, Cosine Measurement:
$$X_{ef,gh}^{(T)} = \frac{|B_{ef}(\text{cosine}, \text{low})| e^{j\phi}}{P^{f+h} a_{gh}^*}$$

High Term, Sine Measurement:
$$X_{ef,gh}^{(S)} = \frac{|B_{ef}(\text{sine}, \text{high})| e^{j\left(\theta - \frac{\pi}{2}\right)}}{P^{f-h} a_{gh}}$$

High Term, Sine Measurement:
$$X_{ef,gh}^{(T)} = \frac{|B_{ef}(\text{sine}, \text{low})| e^{j\left(\phi + \frac{\pi}{2}\right)}}{P^{f+h} a_{gh}^*}$$

→ 4 equations, 4 unknowns.
If phase measurements can be performed, then only two measurements are required.

X-Parameters Research Topics

- Nonlinear Amplifier Design Theory
Paralleling the Linear Design Approach
- Measurement
- Using X-Parameters in Other Disciplines

Nonlinear Amplifier Design with X-Parameters

- Derive equations similar to the small-signal equations such as

$$G_p = \frac{1}{1 - \Gamma_{IN}} |S_{21}|^2 \frac{1 - |\Gamma_L|^2}{|1 - S_{22}\Gamma_L|^2}$$
$$\Gamma_{Ms} = \frac{B_1 \pm \sqrt{B_1^2 - 4|C_1|^2}}{2C_1} \quad \Gamma_{ML} = \frac{B_2 \pm \sqrt{B_2^2 - 4|C_2|^2}}{2C_2}$$

- Calculate and plot gain, stability, third-order intercept (TOI), noise contours on the Smith chart.
- Assess necessary compromises and complete design.
- This may eliminate the arduous “middle-man” of nonlinear transistor modeling. The results also will be based directly on measurement data and will be more accurate!

Measurements

- Typical measurements must be made with a nonlinear vector network analyzer (NVNA) such as the Agilent PNA-X (very expensive).
- Can we measure without a NVNA?
- Vector Signal Analyzer(s), Vector Signal Generator(s) needed for testing of these techniques.
- Could create software routines to automate magnitude and phase calibration at fundamental and considered harmonics.
- To allow a paradigm shift, measurements must be accessible.

Using X-Parameters in Other Disciplines

- Power Electronics
 - Total Harmonic Distortion
 - Characterizing unwanted nonlinearities.
- “Smart” Systems for Clean Power Signals
 - Measure X-parameters of a system.
 - Apply appropriate signal predistortion or system correction to result in a clean signal.
- Vibrations
 - Assess nonlinearities of a vibrational system.
 - Could this be applied to design?

Conclusions

- Nonlinear network functions may be able to revolutionize how nonlinear circuits (and possibly other types of systems) are designed.
- Circuits may be designed directly from nonlinear measurement data; designs will rely less on nonlinear models.
- Associated measurement techniques may save companies money, allowing the paradigm shift to occur.
- Nonlinear network parameters seem to show promise of being useful in other interdisciplinary areas.

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